4-CHANNEL ADPCM VOICE SYNTEHSIS LSI

GENERAL DESCRIPTION

The TT6297/TT6298 is a 4-channel mixing ADPCM voice synthesis LSI which offers one sound outputs with 4 channels . The TT6297/TT6298 can access an external voice data ROM for sound effects or speech voice. The maximum external ROM size is 16M/8M *8 bit and can direct access. The TT6297/TT6298 has an 4-channel synthesis stage which allows the simultaneous playback of four different channels. It is used to have a voice with BGM (Back Ground Music) effect, instrumental sound, echo effect etc.

FEATURES

- Advance ADPCM algorithm
- Number of bits/sample: 4
- 24 address lines (TT6297), 23 address lines (TT6298) for external ROM
- 8-bit control bus for mode setting
- External memory capacity 128Mbit for TT6297/64Mbit for TT6298
- Interface with common CPU and MPU
- Clock frequency with Sampling frequency: (clock 1 MHz to 4 MHz)
 - At 1.088 MHz clock

DAO: 8 kHz

• At 2.176 MHz clock

DAO: 16 kHz

• At 4.352 MHz clock

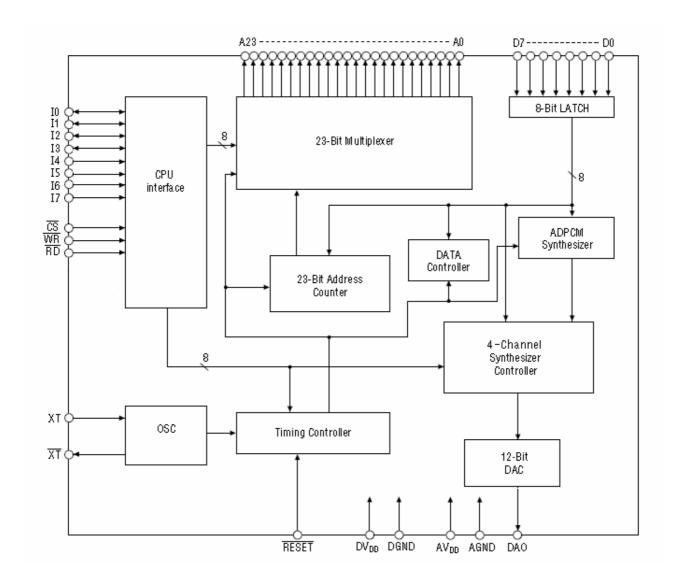
DAO: 32 kHz

- Number of words: 511 maximum
- Vocalization time:TT6297 :64 minutes maximum (at 8 kHz, sample rate)

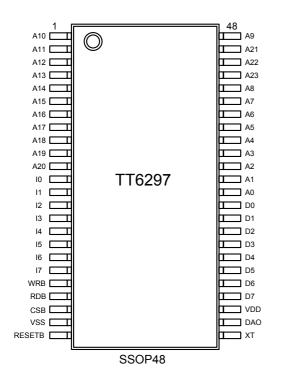
TT6298:32 minutes maximum (at 8 kHz, sample rate)

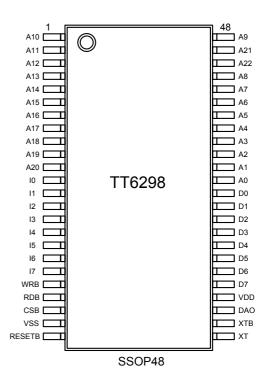
- Sound output channel (DAO with 4 channels)
- Built-in DA converter: 12-bit
- DAO output format: A-class
- Voice level attenuation: OdB~-24dB on each channel (9steps) with -3dB/step
- Advance low power CMOS process
- 5 V or 3.3 V single power supply
- 48-pin plastic SSOP

BLOCK DIAGRAM



PIN CONFIGURATION





TT6297: for external clk input, 24 address lines (A0~A23)

External memory capacity 128Mbit

TT6298: for crystal osc, 23 address lines (A0~A22)

External memory capacity 64Mbit

PIN DESCRIPTION

Pin Name	Pin NO TT6297	Pin NO TT6298	I/O	Function
$I_0 \sim I_3$	12~15	12~15	I/O	Instruction bus and condition outputs.
				These pins are inputs for phrase specification
				Maximum number of phrases is 511, $l_0 \sim l_3$ pins are
$I_{4} \sim I_{7}$	16~19	16~19	I	also outputs of the operating state- busy state, for
				channels 1~4 and are further used to select the
HADD	20	20	т .	channel attenuation rate.
WRB	20	20	I	Write enable input. Data is written on the data bus
				of $l_0 \sim l_7$ The data is written when \overline{WR} goes low.
RDB	21	21	I	Read enable input.
				The output busy state of channels 1~4 on the data
				bus of $l_0 \sim l_3$ can be read using this input. A high level
CCD	22	22	т	indicates busy.
CSB	22	22	I	Chip select input. Input "L" level either when
				WR signal is input or when RD signal is input.
RESETB	24	24	I	Reset input. Reset condition is available by
				inputting "L" level
	26.40	27. 40		All functions are suspended during reset.
$A_{0} A_{23}$	36~48 1~11	37~48 1~11	О	Address outputs.
$/ A_{22}$	1~11	1~11		These pins are to address the external ROM in
				which voice data is stored.
				TT6297: A0~A23
D D	28~35	29~36	т	TT6298: A0~A22
$\begin{array}{c} D_0 \sim D_7 \\ \hline DAO \end{array}$	26~33	27~30	O	Voice data inputs. Voice synthesis output.
DAO	20	27	U	Voice synthesized analog signal is output from
				this pin.
XT	25	25	I	External clk input (Crystal oscillator pin.).
XTB	_	26	0	Crystal oscillator pin.
VDD	28	28	P	Power Supply pin.
VSS	23	23	P	Ground pin.

ELECTRICAL CHARACTERISTICS

• Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Power supply voltage	VDD	Ta=25°C	-0.3~+7.0	V
Input voltage	V _{IN}	Ta=25°C	-0.3~VDD +0.3	V
Storage temperature	T_{stg}		- 55 ∼ 150	°C

• Recommended Operating Conditions

Parameter	Symbol	Conditions	Value	Unit
Power supply voltage	VDD	VSS=0V	2.9 ~ +5.5	V
Operating temperature	Top	VSS=0V	- 40 ∼ +85	°C
Oscillation frequency	f_{osc}	VSS=0V	1~5	MHz

• DC Characteristics

$$(Vdd = 2.9 \sim 5.5V, VSS=0V, Ta = -40 \sim 85^{\circ}C)$$

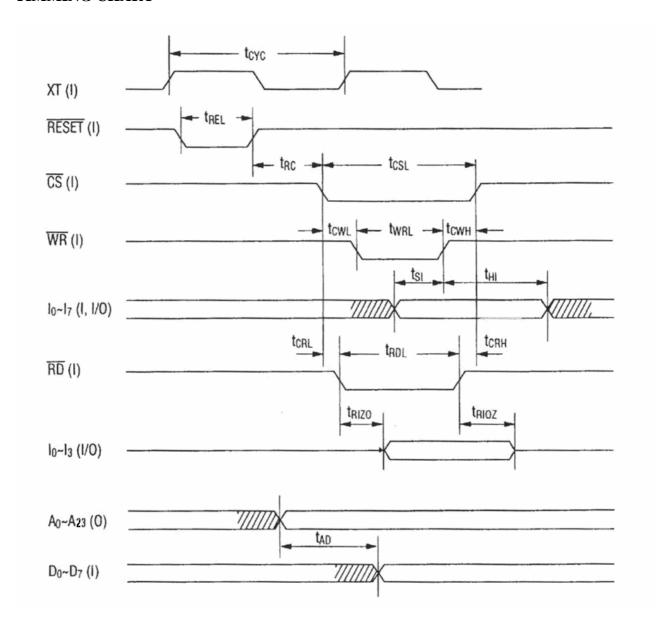
Parameter	Symbol	Conditions		Unit			
1 at affecter	Symbol	Conditions	Min.	Typ.	Max.	Omt	
"L" input current	$ m I_{IL}$	V _{IL} =VSS	-10	1	1	^	
"H" input current	$ m I_{IH}$	V _{IH} =VDD	I		10	μΑ	
"L" input voltage	$ m V_{IL}$	_	1		0.2Vdd	V	
"H" input voltage	$V_{ m IH}$	_	0.8Vdd	1	1	v	
"L" output voltage	$ m V_{OL}$	$I_{LO}=0.8$ mA	I		0.45	V	
"H" output voltage	V_{OH}	I_{OH} =-40 μ A	Vdd		_	v	
Output leakage current	I_{LO}	VSS≤V _{OUT} ≤VD D	-10	l	10	μΑ	
Operating current	I_{DD}	f_{OSC} =4.0MHz	l	5	10	mA	
DA output relative error	V_{DAE}	No load		_	20	mV	
DA output impedance	R _{DAOUT}	_	_	15	_	$\mathrm{k}\Omega$	

• AC Characteristics

 $VDD = 4.5 \sim 5.5 \text{V,VSS} = 0 \text{V,Ta} = -40 \sim +85 ^{\circ}\text{C}$

Parameter	Symbol	Min.	Тур	Max.	Unit
Clock cycle	t_{CYC}	200	-	-	ns
Clock duty cycle	f_{DUTY}	40	50	60	%
RESET pulse width	$t_{ m REL}$	100	-	-	ns
CS pulse width	t_{CSL}	250	-	-	ns
WR pulse width	t_{WRL}	200	-	-	ns
RD pulse width	$t_{ m RDL}$	300	-	-	ns
\overline{RESET} fall to \overline{CS} fall	t_{RC}	250	-	-	ns
\overline{CS} fall to \overline{WR} fall	t_{CWL}	50	•	1	ns
\overline{WR} raise to \overline{CS} raise	t_{CWH}	0	-	-	ns
Data set up time of I_0 - I_7 in respect to	t _{SI}	80	-	-	ns
WR raise					
Data hold time of I_0 - I_7 in respect to \overline{WR}	t _{HI}	80	-	-	ns
raise					
\overline{RD} fall to stable output of I_0 - I_3	t_{RIZO}	-	-	120	ns
\overline{RD} raise to flow status output of I_0 - I_3	t_{RIOZ}	0	-	120	ns
\overline{CS} fall to \overline{RD} fall	t_{CRL}	20	•	1	ns
\overline{RD} raise to \overline{CS} raise	t_{CRH}	0	-	-	ns
Address stable (A ₀ -A ₂₃) to data input of	t_{AD}	-	-	5•t _{CYC} +90	ns
D_0 - D_7					

TIMMING CHART



FUNCTION EXPLANATION

1. Phrase Selection

Phrase Selection Phrases are specified and read into the 2 byte data which consists of $I_0 \sim I_7$ data bus. The phrase selection data is latched when WRB goes high while CSB is low .The format of the phrase specification input is as follows.

 I_7 I_6 I_5 I_4 I_3 I_2 I_1 I_0 1 Phrase selection data 1st Byte Reduction specification Phrase expansion II6,II7 & 2nd Byte **Channel specification II4,II5** II3~II0

Relation between Phrase Selection Data and ROM Address

Phrase Selection		Il_7	Il_6	1.	15	14	1.	1.	1.	1.			
Data		117	116	l_6	15	14	l ₃	12	l_1	I_0	-	_	-
External ROM address	A ₂₃ ~A ₁₀	A ₁₁	A ₁₀	A ₉	A ₈	A ₇	A_6	A_5	A_4	A ₃	A_2	A_1	A_0
Selection													
Not valid	0~0	0	0	0	0	0	0	0	0	0	0	0	0
Phrase 1	0~0	0	0	0	0	0	0	0	0	1	0	0	0
Phrase 2	0~0	0	0	0	0	0	0	0	1	0	0	0	0
Phrase 3	0~0	0	0	0	0	0	0	0	1	1	0	0	0
Phrase 510 Phrase 511	0~0 0~0	1 1	1 1	1	1	1	1 1	1	1	0	0	0	0

^{*} Phrases can not be specified with all inputs = "0"

The second byte of data specifies the high phrase address, the synthesis operating channel as well as specific channel reduction of the synthesized play-back. The channel selection format is shown below. It is not possible to specify multiple channels at the same time.

Phrase expansion bits

The data bits II7 & II6 of second byte and the data bits I6~I0 of first byte will Combine as the total phrase address A11~A3.

Channel Specification

Channe I	II_5	II_4
1	0	0
2	0	1
3	1	0
4	1	1

Reduction Specification

All zero is considered as 0 dB of the relative sound itself. The reduction is made through 9 levels from about 0 dB to - 24 dB with the steps of about - 3 dB. Reduction format is shown below.

Reduction Selection

Attenuation level	l ₃	l ₂	I ₁	I ₀
0dB	0	0	0	0
-3.2 dB	0	0	0	1
-6.0 dB	0	0	1	0
-9.2 dB	0	0	1	0
-12.0dB	0	1	0	0
-14.5dB	0	1	0	1
-18.0dB	0	1	1	0
-20.5dB	0	1	1	1
-24.0dB	1	0	0	0

2. Voice Synthesis Channel Suspension

Voice synthesis operation of any channel can be suspended. Channel suspension is controlled by bits $I_3 \sim I_6$ of data bytes $I_0 \sim I_{07}$. To suspend a channel, make $I_7 = 0$, while $I_3 \sim I_6$ represent the channels which should be suspended Channel suspension occurs even if multiple channels are selected. For example, if $I_3 \sim I_6$ are all 1 and $I_7 = 0$, then channels $1 \sim 4$ are suspended simultaneously.

Suspended channel	l ₇	I ₆	l ₅	I ₄	I ₃	l ₂	I ₁	I ₀
1	0	0	0	0	1	×	×	×
2	0	0	0	1	0	×	×	×
3	0	0	1	0	0	×	×	×
4	0	1	0	0	0	×	×	×

3.Data ROM

1) ADDRESS DATA

This specifics start and stop address of ADPCM speech data. One phrase start and end address consists of 8 bytes. The first 3 bytes show start address while the last 3 bytes show stop address. The other 2 bytes are empty. By selecting the first address in which the start address is stored, the selected speech data is played back.

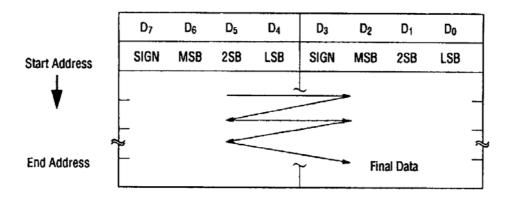
Address 0	SA_1
Address 1	SA_2
Address 2	SA_3
Address 3	EA_1
Address 4	EA ₂
Address 5	EA ₃
Address 6	EMPTY
Address 7	EMPTY

Start addresses ($SA_1 \sim SA_3$) and stop addresses ($EA_1 \sim EA_3$) are stored according to the chart shown below

	D ₇	D_6	D_5	D_4	D_3	D_2	D_1	D_0
SA_1/EA_1	A23	A22	A21	A20	A19	A18	A ₁₇	A ₁₆
SA_2/EA_2	A_{15}	A_{14}	A_{13}	A_{11}	A_{10}	A_{15}	A_9	A_8
SA ₃ / EA ₃	A_7	A_6	A_5	A_3	A_2	A ₁₅	A_1	$\overline{A_0}$

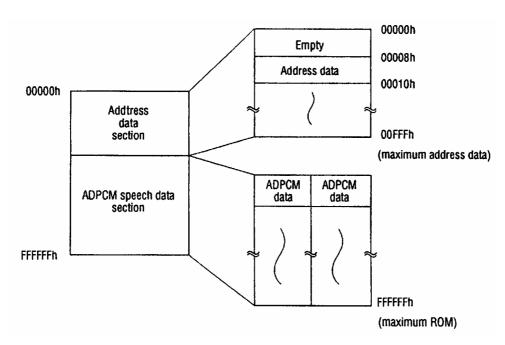
2) ADPCM SPEECH DATA

ADPCM speech data consists of 4-bit samples. So, 1 byte stores 2 samples. The data arrangement proceeds from higher rank bits $(D_4 \sim D_7)$ to lower rank bits $(D_0 \sim D_3)$. The storage of speech data should always be ended with the lower rank bit, So, always store an even number of samples, Speech data is produced by Speech Development Tool TT6297/TT6298.



3) DATA ROM STRUCTURE

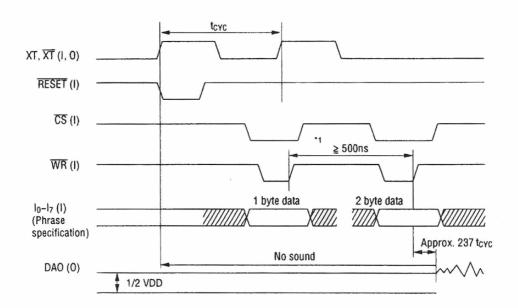
When 1 phrase is selected, address data is written from ROM address 00008h to 0000Fh, When the maximum 511 phrases are selected in address data section, the data is written up to ROM address 00FFFh. and the rest is used as the ADPCM data section. The following chart shows the memory map of the source data ROM.



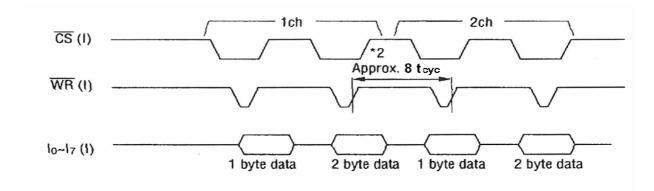
FUNCTIONAL DESCRIPTION

1. Phrase Selection Input

This procedure is to input phrase selection data onto the data bus inputs $I_0 \sim I_7$. The data is latched internally when \overline{WR} rises from "L" to "H", while CSB remains "L". Voice synthesis operation does not start till the second byte is fully latched



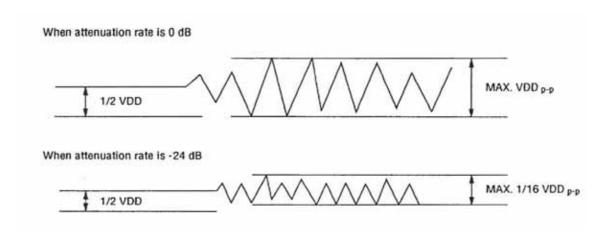
Note: Phrase selection is from channel 1 to channel 8 continuously
If all of CH1~CH4 CMM are latched, then the DAO output Arrrox.. 420 tcyc.
*1 An interval of 75 T_{CYC} (max.) is needed between phrases



Note*2 Oscillation frequency = 1.088 MHz SS = "L'

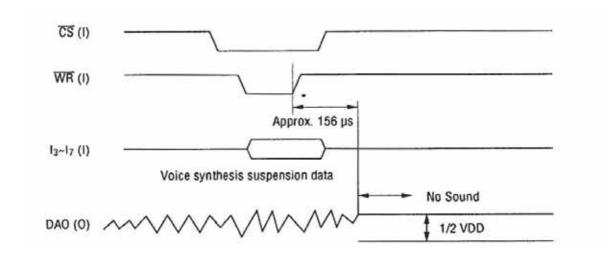
Voice synthesis playback can be started from any channel, l to 8. The arrangement of each channel can be in any order. The second byte of the phrase selection data contains the phrase attenuation data in bits D_0 - D_3 . Synthesized data is attenuated in -3 dB steps from 0 dB to -24 dB.

2. Attenuation of Synthesized Speech



3. Speech Synthesis Channel Suspension

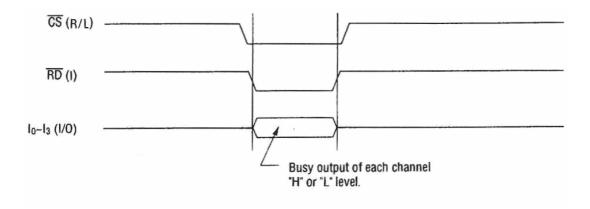
This is accomplished by writing the synthesis channel suspension data onto data bus inputs $I_3 \sim I_7$ The data is latched internally when $\overline{\text{WR}}$ goes from "L" to "H" while CSB remains active (L). Since synthesis suspension data is 1 byte data, synthesis operation is suspended right after the rising edge of $\overline{\text{WR}}$. Multiple channels can be specified, making it possible to suspend channels $1 \sim 4$ simultaneously.



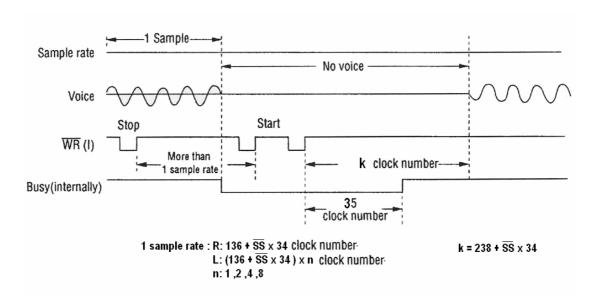
Note: * Oscillation frequency = 1.088 MHz SS= "L"

4. Reading the Busy Status

While CSB is "L" and \overline{RD} is "L", each operation state, the busy state of channels 1~4 is output on $I_0\sim I_3$. "H" is output during synthesized playback.

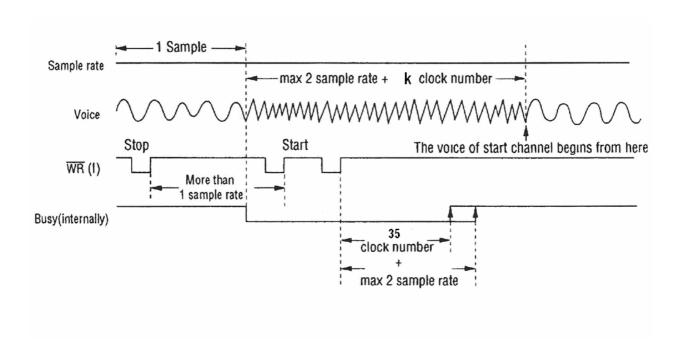


5. Start and Stop of 1 Channel



Start and Stop of Signal Channel

When a single channel (either of channels 1-4) starts again after it has stopped, the first write for start must be input with a delay of more than one sample rate from the stop write as shown in the figure above. When stop is entered, voice playback stops all the next sample and BUSY becomes "L" When start is entered again, voice is output after 238 + (the reverse of SS pin) x 34 clock from the second byte write. BUSY becomes "H" after 35 clock internally

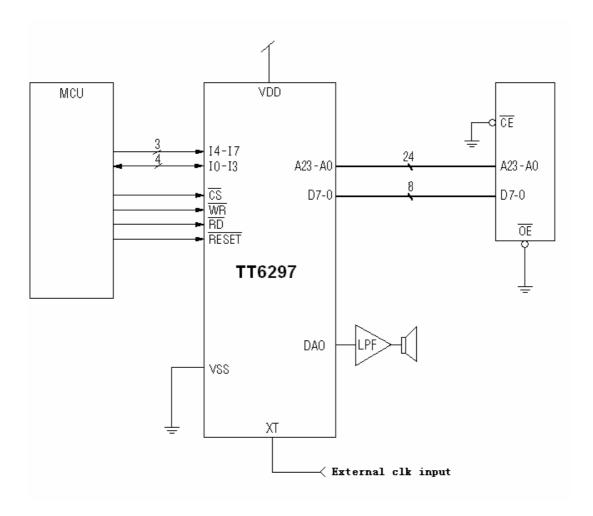


Start and Stop in Plural Channels

When channels are operating, the first byte write for start must be input with a delay of more than one sample rate from stop writing. The channel where stop was input, stops at every sample. Voice off the channel where stop was again input is output after a maximum 2 samples +k clocks from the preceding sample point.

The BUSY signal becomes "H" state after the 35 clock + maximum 2 samples time.

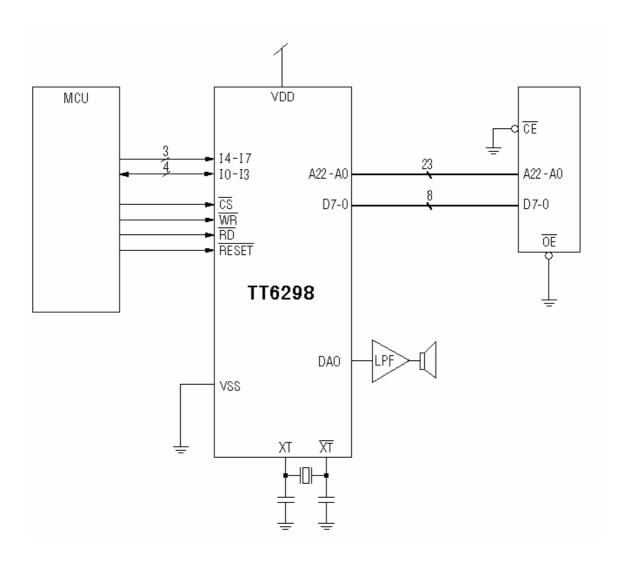
APPLICATION CIRCUIT FOR TT6297



TT6297 : for external clk input , 24 address lines (A0~A23) External memory capacity 128Mbit

Reference Only

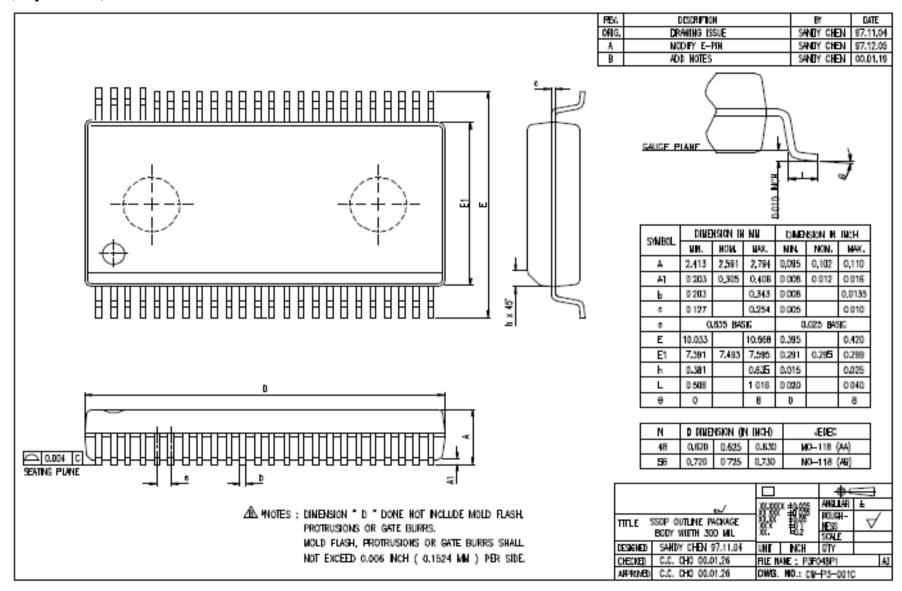
APPLICATION CIRCUIT FOR TT6298



TT6298 : for crystal osc , 23 address lines (A0~A22) External memory capacity 64Mbit

Reference Only

(48 pin SSOP)



REVISE HISTORY

- 1. 2007/6/20 (V1.0)
 - -Original version